ABSTRACT

Forming Method and Forming System of Insulation Film

A gate insulation film (104) of a MISFET (100) is constituted of a silicon oxide film (106), silicon nitride film (107), and high-permittivity film (108). The silicon oxide film (106) and silicon nitride film (107) are formed by microwave plasma processing with a radial line slot antenna.

[FIG. 1]